

Notice of References Cited	Application/Control No. 10/721,065		Applicant(s)/Patent Under Reexamination STRASSBURG ET AL.	
	Examiner Savitri Mulpuri		Art Unit 2812	Page 1 of 1

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*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
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NON-PATENT DOCUMENTS

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*	U	Honda et al, "fromation of highly conductive p-type ZnSe using lithium nitride diffusion" Jpn Appl Phys, Vol.35(no.7) p3878-9(apr 1998)			
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*	W	Lim et al "High p-type doping of ZnSe using lithium nitride diffusion" applied Physcls Letters Vo.65(no.19) p2437-8(nOv 7, 1994)			
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*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)
Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.